

## Switchmode Dual High Efficiency Power Rectifiers

... Designed for use in switching power supplies. inverters and as free wheeling diodes. These state-of-the-art devices have the following features:

- \* High Surge Capacity
- \* Low Power Loss, High efficiency
- \* Glass Passivated chip junctions
- \* 150 °C Operating Junction Temperature
- \* Low Stored Charge Majority Carrier Conduction
- \* Low Forward Voltage , High Current Capability
- \* High-Switching Speed 50 Nanosecond Recovery Time
- \* Plastic Material used Carries Underwriters Laboratory

## **MAXIMUM RATINGS**

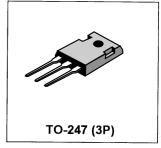
Characteristic	Symbol	H30D				Unit
		05	10	15	20	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	50	100	150	200	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	35	70	105	140	V
Average Rectifier Forward Current Per Leg T <sub>c</sub> =125°C Per Total Device	I <sub>F(AV)</sub>		1 3	5 0		А
Peak Repetitive Forward Current (Rate V <sub>R</sub> , Square Wave, 20kHz, T <sub>C</sub> =125°C)	I <sub>FM</sub>		3	0		Α
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware,single phase,60Hz)	  FSM		25	50		А
Operating and Storage Junction Temperature Range	T <sub>j</sub> , T <sub>stg</sub>		- 65 to	+ 150		°C

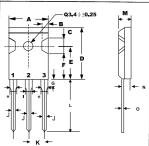
## **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol		Unit			
		05	10	15	20	7
Maximum Instantaneous Forward Voltage $(I_F=15 \text{ Amp}, T_c=25 ^{\circ}\text{C})$ $(I_F=15 \text{ Amp}, T_c=100 ^{\circ}\text{C})$	V <sub>F</sub>			00 87		V
Maximum Instantaneous Reverse Current (Rated DC Voltage, T <sub>c</sub> = 25 °C) (Rated DC Voltage, T <sub>c</sub> = 125 °C)	I <sub>R</sub>	10 700			uA	
Reverse Recovery Time ( $I_F = 0.5 \text{ A}, I_R = 1.0, I_{rr} = 0.25 \text{ A}$ )	T <sub>rr</sub>		5	0		ns
Typical Junction Capacitance ( Reverse Voltage of 4 volts & f=1 MHz)	C <sub>P</sub>		2	50		pF

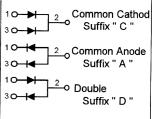
HIGH EFFICIENCY RECTIFIERS

**30 AMPERES 50 -- 200 VOLTS** 





DIM	MILLMETERS			
D.I.V.	MIN	MAX		
Α		16.2		
В	1.7	2.7		
С	5.0	6.0		
D		23.0		
Ε	14.8	15.2		
F	11.7	12.7		
G		4.5		
Н		2.5		
ı		3.5		
J	1.1	1.4		
K	5.25	5.65		
L	19			
М	4.7	5.3		
N	2.8	3.2		
0	0.45	0.85		



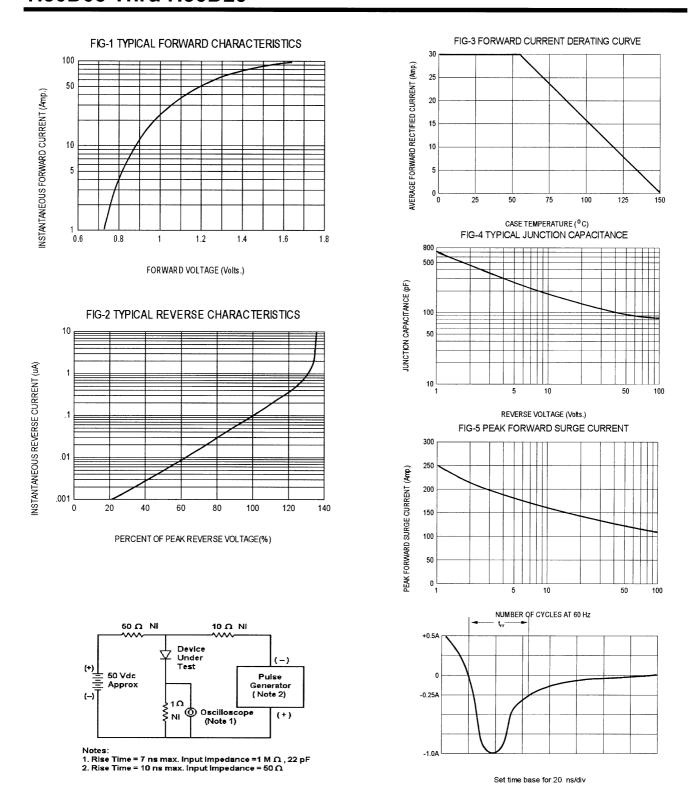


Fig-6 Reverse Recovery Time Characteristic and Test Circuit Diagram



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